

# APM3054N

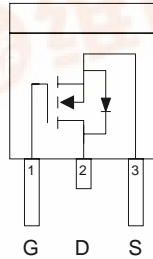


N-Channel Enhancement Mode MOSFET

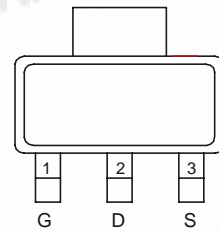
## Features

- 30V/15A,  $R_{DS(ON)}=48m\Omega(\text{typ.}) @ V_{GS}=10V$   
 $R_{DS(ON)}=75m\Omega(\text{typ.}) @ V_{GS}=4.5V$
- Super High Dense Cell Design
- High Power and Current Handling Capability
- TO-252 and SOT-223 Package

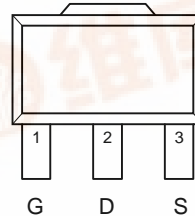
## Pin Description



Top View of TO-252



Top View of SOT-223



Top View of SOT-89

## Applications

- Switching Regulators
- Switching Converters

## Ordering and Marking Information

APM3054N	Package Code D : SOT-89    U : TO-252    V : SOT-223 Operating Junction Temp. Range C : -55 to 125° C Handling Code TR : Tape & Reel
APM3054N U :	XXXXX - Date Code
APM3054N D/V :	XXXXX - Date Code

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$I_D$	Maximum Drain Current – Continuous	15	A
$I_{DM}$	Maximum Drain Current – Pulsed	30	
$I_S$	Diode Continuous Forward Current	8	A

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.



## Absolute Maximum Ratings (Cont.) ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

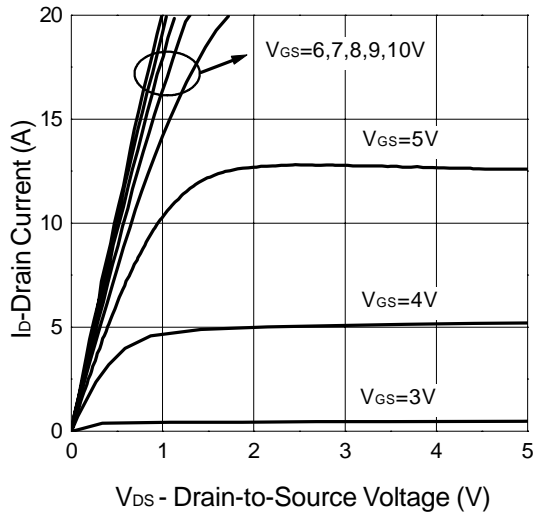
Symbol	Parameter		Rating	Unit	
$I_{SM}$	Diode Maximum Pulse Current		32	A	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	TO-252	62.5	W
			SOT-223	3	
		$T_A=100^\circ\text{C}$	TO-252	25	W
			SOT-223	1.2	
$T_J$	Maximum Junction Temperature		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range		-55 to 150	$^\circ\text{C}$	

## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

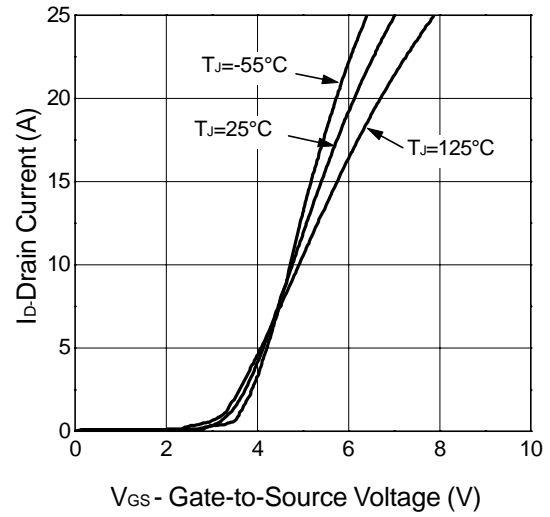
Symbol	Parameter	Test Condition	APM3054N			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$			1	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1		3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=12A$		48	54	m $\Omega$
		$V_{GS}=4.5V, I_{DS}=6A$		75	90	
$V_{SD}$	Diode Forward Voltage	$I_{SD}=8A, V_{GS}=0V$	0.6		1.3	V
<b>Dynamic</b>						
$Q_g$	Total Gate Charge	$V_{DS}=15V, V_{GS}=5V, I_{DS}=10A$		9		nC
$Q_{gs}$	Gate-Source Charge			5.4		
$Q_{gd}$	Gate-Drain Charge			2.4		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, I_D=2A, V_{GS}=10V, R_G=6\Omega$		11		ns
$t_r$	Turn-on Rise Time			17		
$t_{d(OFF)}$	Turn-off Delay Time			37		
$t_f$	Turn-off Fall Time			20		
$C_{iss}$	Input Capacitance	$V_{GS}=0V$		400		pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$		75		
$C_{rss}$	Reverse Transfer	Frequency=1.0MHz		45		

## Typical Characteristics

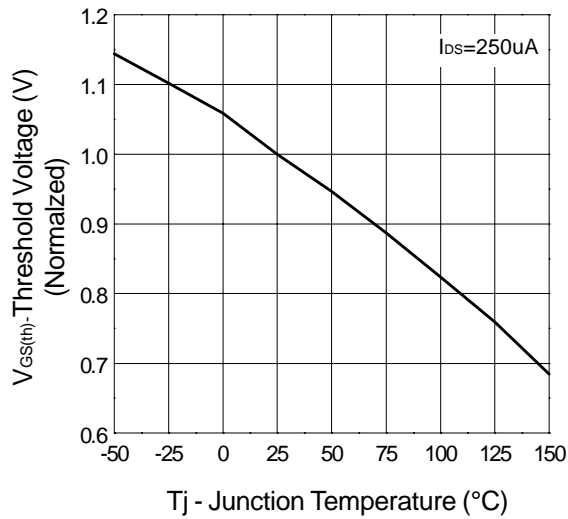
Output Characteristics



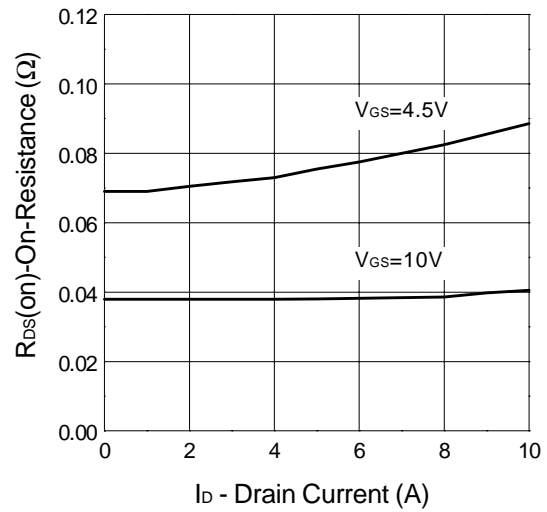
Transfer Characteristics



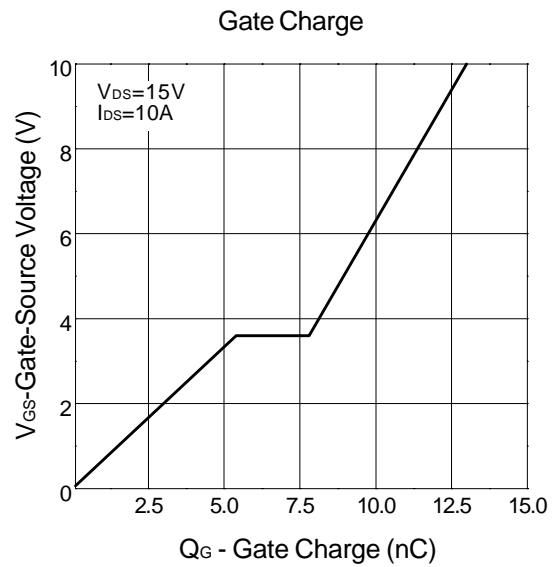
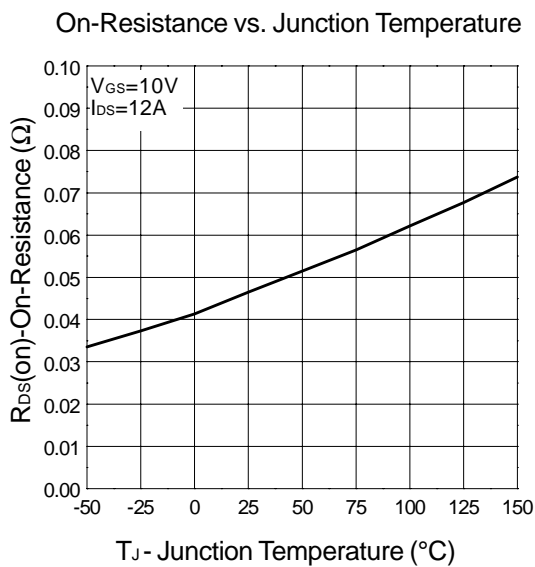
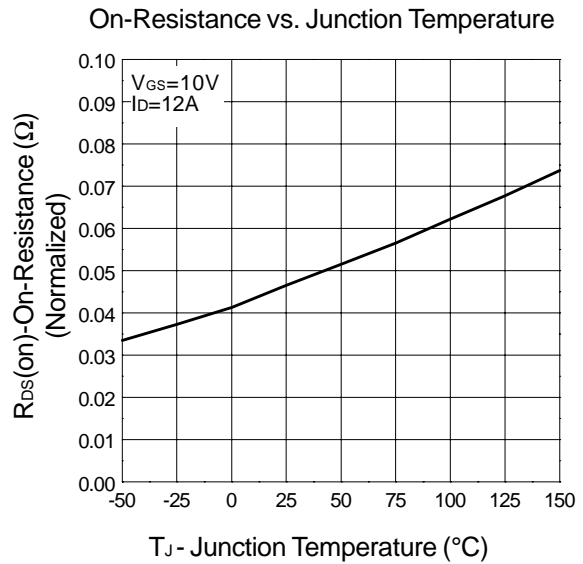
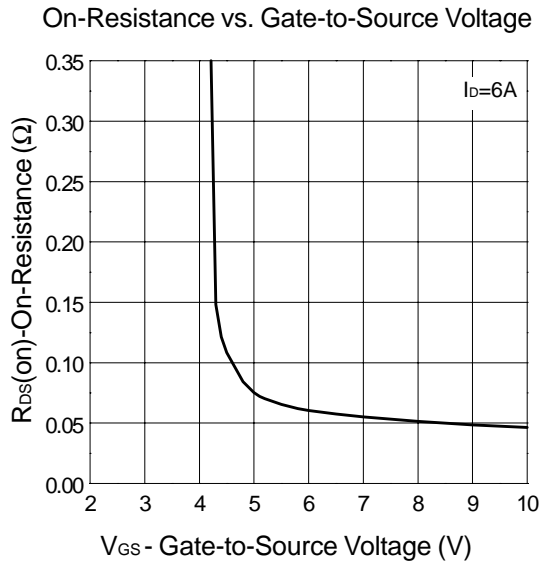
Threshold Voltage vs. Temperature



On-Resistance vs. Drain Current

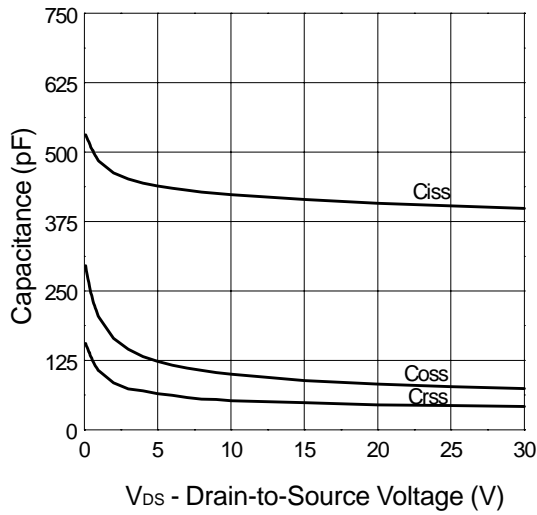


## Typical Characteristics

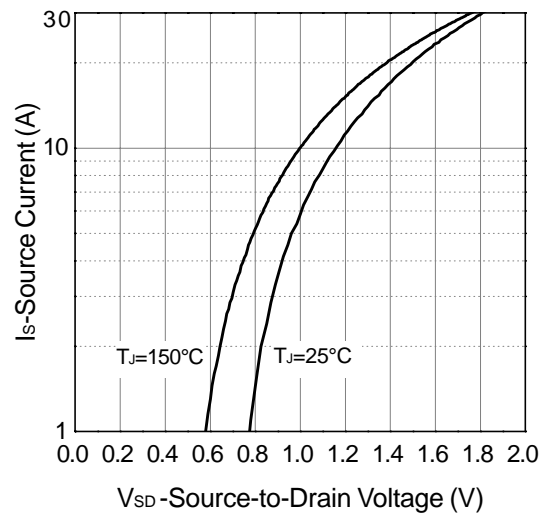


## Typical Characteristics

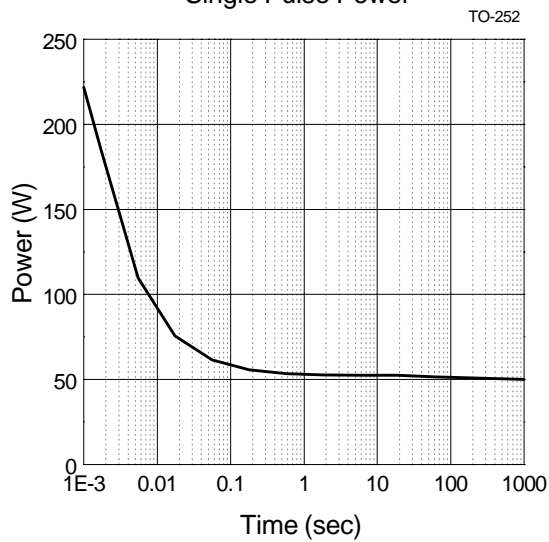
Capacitance



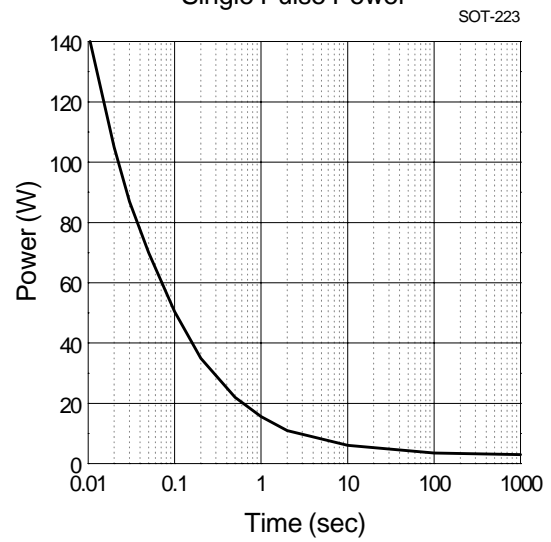
Source-Drain Diode Forward Voltage



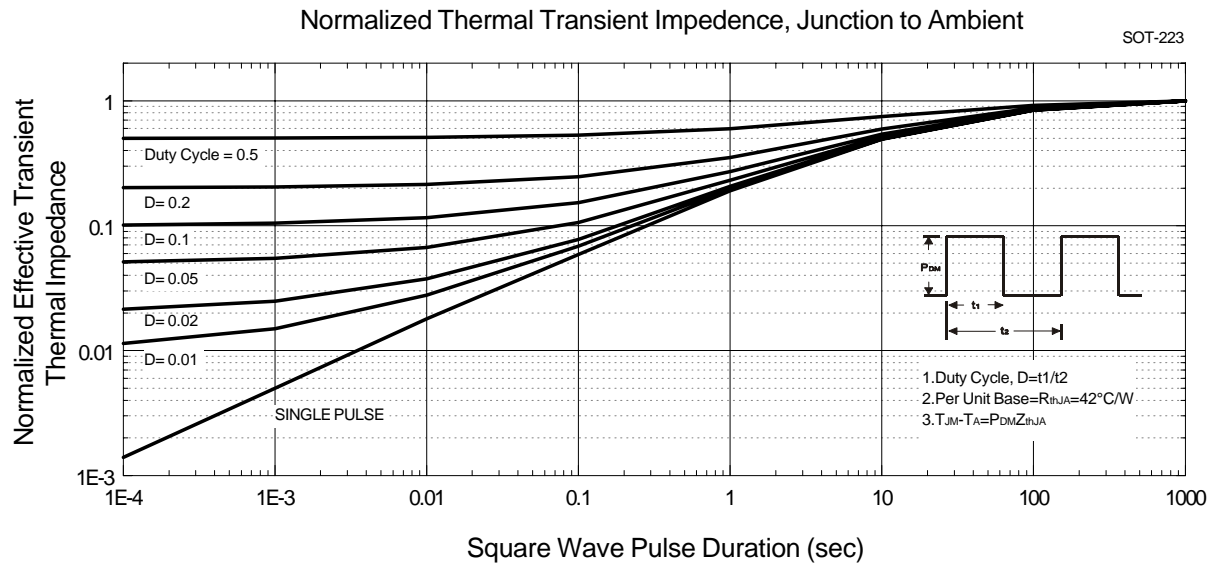
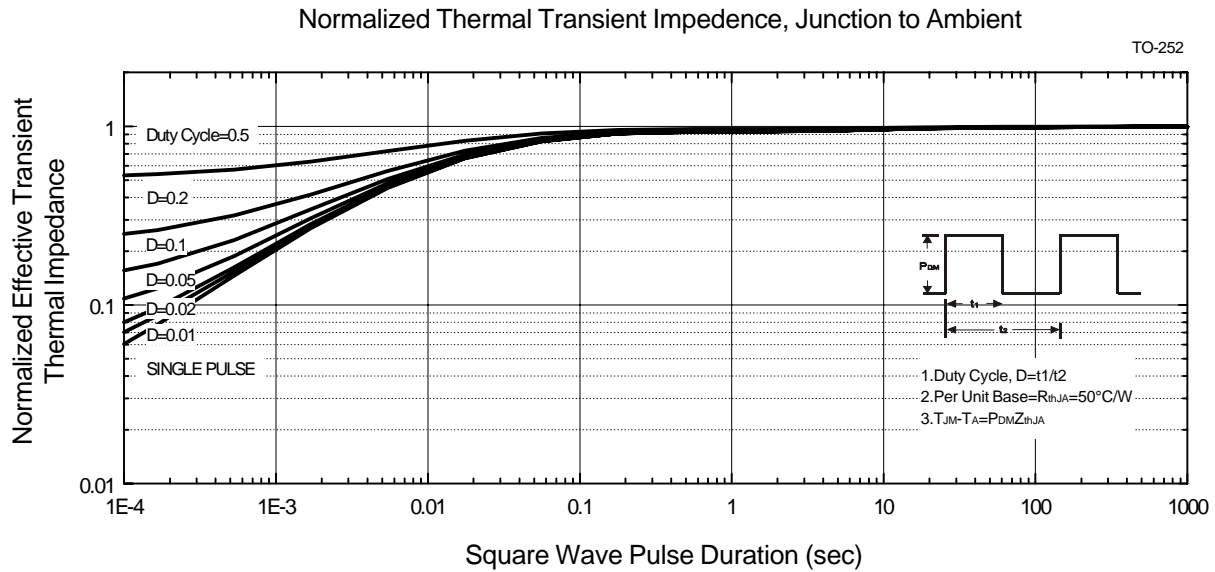
Single Pulse Power



Single Pulse Power

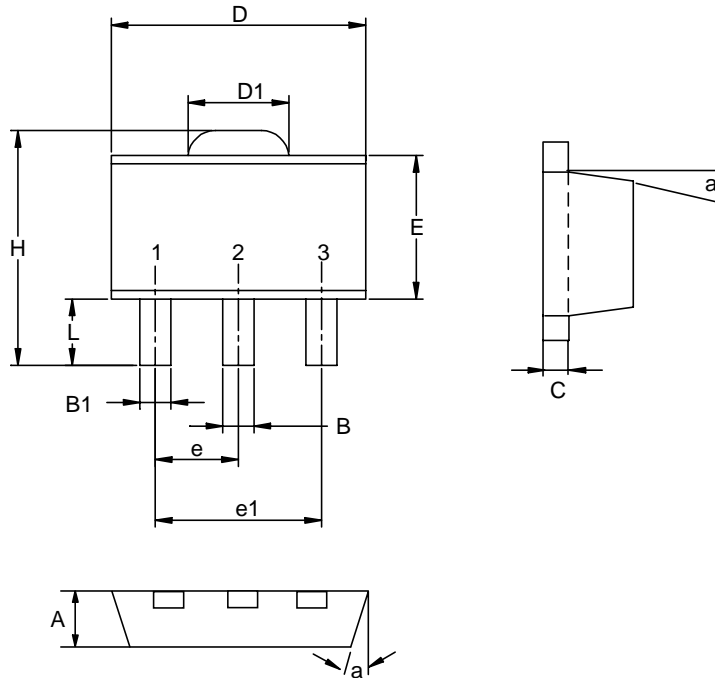


## Typical Characteristics



## Package Information

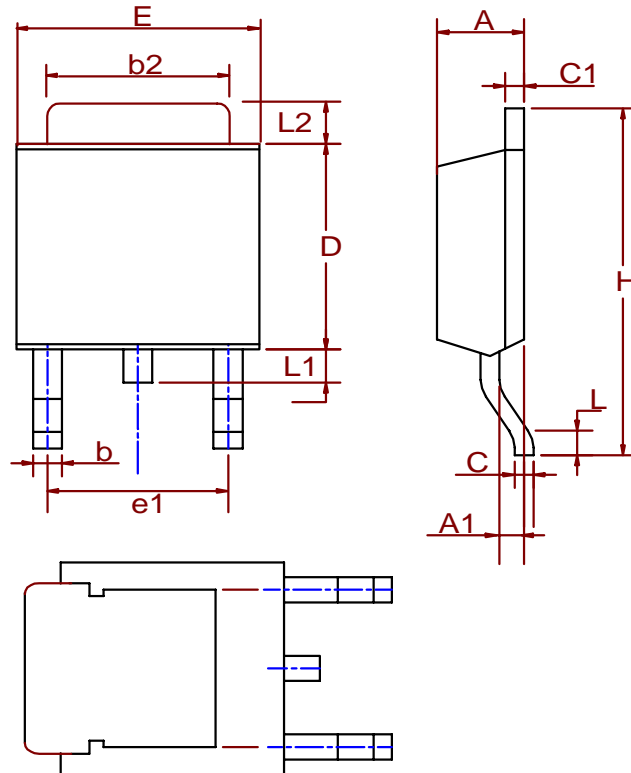
SOT-89 (Reference EIAJ ED-7500A Registration SC-62)



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.50 BSC		0.059 BSC	
e1	3.00 BSC		0.118 BSC	
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047
$\alpha$		10°		10°

## Package Information

TO-252( Reference JEDEC Registration TO-252)

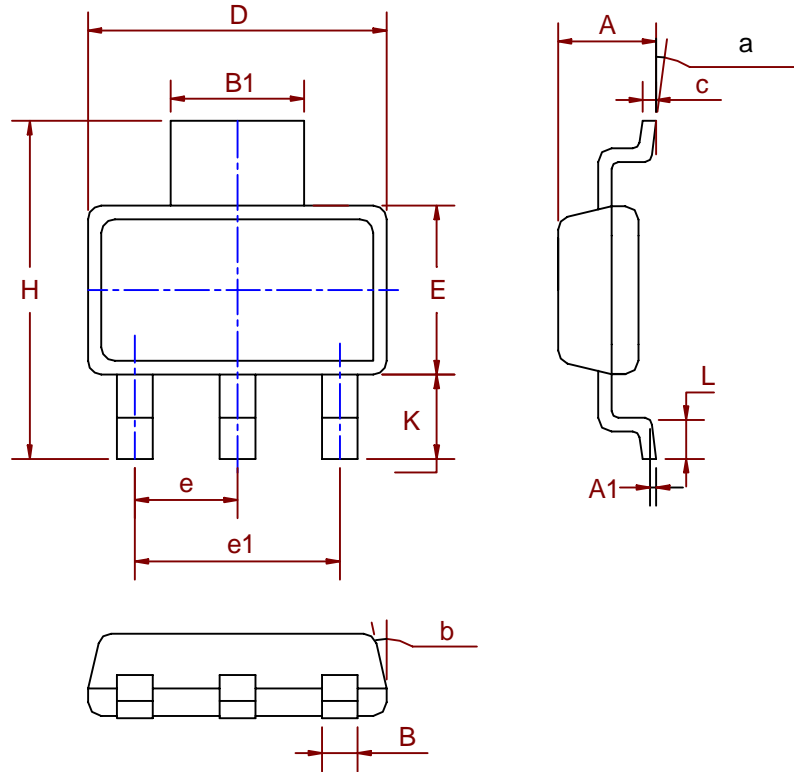


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
E	6.35	6.73	0.250	0.265
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080



## Package Information

SOT-223( Reference JEDEC Registration SOT-223)



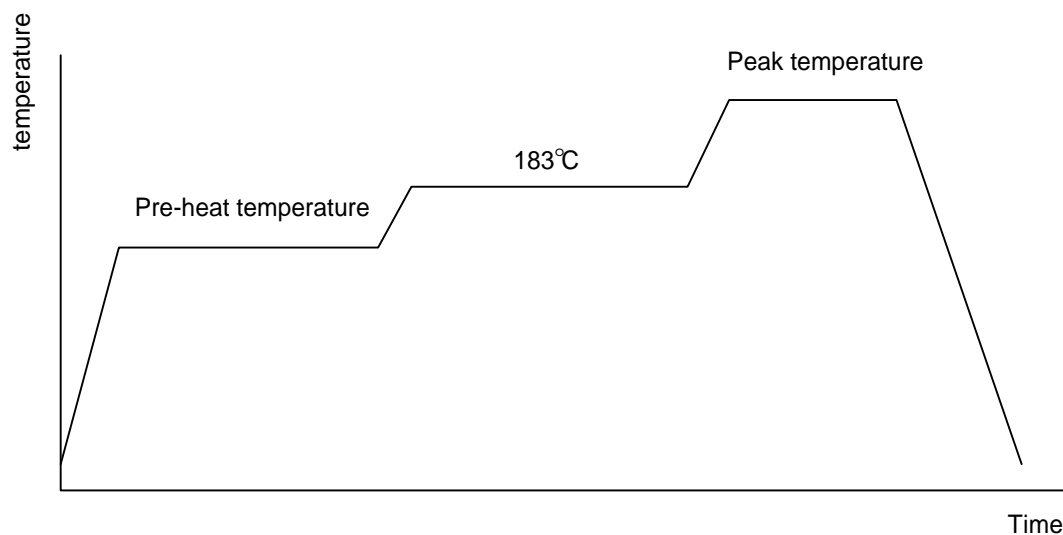
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.50	1.80	0.06	0.07
A1	0.02	0.08		
B	0.60	0.80	0.02	0.03
B1	2.90	3.10	0.11	0.12
c	0.28	0.32	0.01	0.01
D	6.30	6.70	0.25	0.26
E	3.30	3.70	0.13	0.15
e	2.3 BSC		0.09 BSC	
e1	4.6 BSC		0.18 BSC	
H	6.70	7.30	0.26	0.29
L	0.91	1.10	0.04	0.04
K	1.50	2.00	0.06	0.08
α	0°	10°	0°	10°
β	13°		13°	

## Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

## Reflow Condition (IR/Convection or VPR Reflow)

Reference JEDEC Standard J-STD-020A APRIL 1999



## Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183°C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25°C)	120 seconds max	
Temperature maintained above 183°C	60 – 150 seconds	
Time within 5°C of actual peak temperature	10 –20 seconds	60 seconds
Peak temperature range	220 +5/-0°C or 235 +5/-0°C	215-219°C or 235 +5/-0°C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25°C to peak temperature	6 minutes max.	

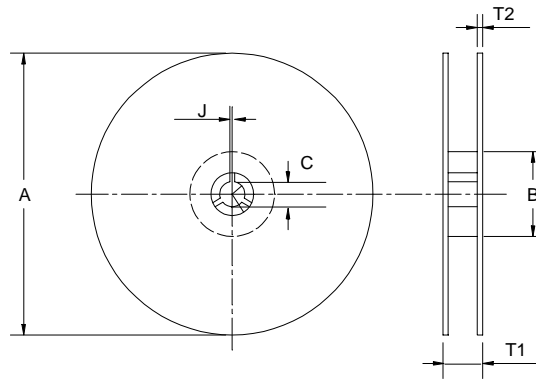
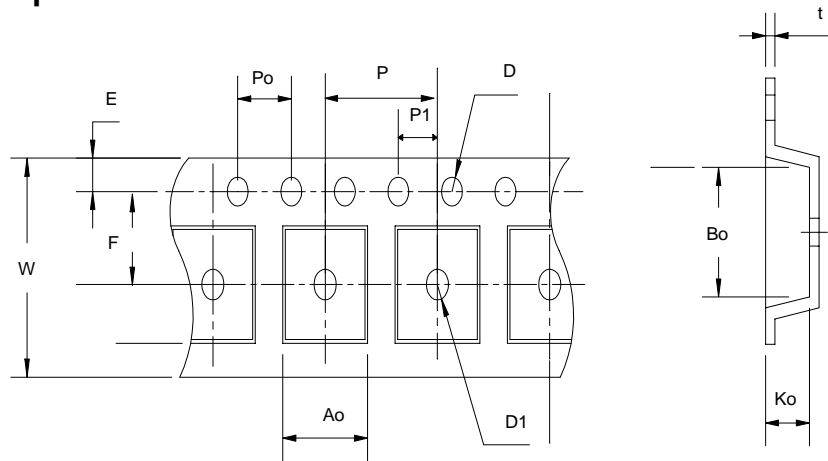
## Package Reflow Conditions

pkg. thickness ≥ 2.5mm and all bgas	pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm <sup>3</sup>	pkg. thickness < 2.5mm and pkg. volume < 350mm <sup>3</sup>
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

### Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C , 5 SEC
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @ 125 °C
PCT	JESD-22-B, A102	168 Hrs, 100 % RH , 121°C
TST	MIL-STD-883D-1011.9	-65°C ~ 150°C, 200 Cycles
ESD	MIL-STD-883D-3015.7	VHBM > 2KV, VMM > 200V
Latch-Up	JESD 78	10ms , I <sub>tr</sub> > 100mA

### Carrier Tape



<b>Application</b>	A	B	C	J	T1	T2	W	P	E
<b>SOT-89</b>	178 ±1	70 ±2	13.5 ± 0.15	3 ± 0.15	14 ± 2	1.3 ± 0.3	12 + 0.3 12 - 0.1	8 ± 0.1	1.75 ± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.05	1.5 ± 0.1	1.5 ± 0.1	4.0 ± 0.1	2.0 ± 0.1	4.8 ± 0.1	4.5 ± 0.1	1.80 ± 0.1	0.3 ± 0.013
<b>Application</b>	A	B	C	J	T1	T2	W	P	E
<b>TO-252</b>	330 ±3	100 ± 2	13 ± 0.5	2 ± 0.5	16.4 + 0.3 -0.2	2.5 ± 0.5	16 + 0.3 -0.1	8 ± 0.1	1.75 ± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ± 0.1	1.5 ± 0.1	1.5 ± 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4 ± 0.1	2.5 ± 0.1	0.3 ± 0.05
<b>Application</b>	A	B	C	J	T1	T2	W	P	E
<b>SOT-223</b>	330 ±1	62 ± 1.5	12.75 ± 0.15	2 ± 0.6	12.4 ± 0.2	2 ± 0.2	12 ± 0.3	8 ± 0.1	1.75 ± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.05	1.5 ± 0.1	1.5 ± 0.1	4.0 ± 0.1	2.0 ± 0.05	6.9 ± 0.1	7.5 ± 0.1	2.1 ± 0.1	0.3 ± 0.05

## Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
<b>SOT- 89</b>	12	9.3	1000
<b>SOT- 223</b>	12	9.3	2500
<b>TO- 252</b>	16	13.3	2500

## Customer Service

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